

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	42	(pecvd (plasma near2 (cvd (chemical adj vapor)))) same (tft (thin adj film adj transistor)) same ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h"))	US-PGPUB; USPAT	OR	ON	2006/03/30 13:47
L3	291	438/792.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/30 13:17
L4	66	(tft (thin adj film adj transistor)) and ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h"))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/30 13:32
L5	64	(pecvd (plasma near2 (cvd (chemical adj vapor)))) and ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h"))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/30 13:34
L6	2152	438/151.ccls. 438/475.ccls. 438/791.ccls. 438/792.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/30 13:36
L7	52	L6 and ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h"))	US-PGPUB; USPAT	OR	ON	2006/03/30 13:36
L9	1	((pecvd (plasma near2 (cvd (chemical adj vapor)))) and (tft (thin adj film adj transistor)) and ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h")).clm.	US-PGPUB	OR	ON	2006/03/30 13:48
L10	23	((pecvd (plasma near2 (cvd (chemical adj vapor)))) (tft (thin adj film adj transistor))) and ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h")).clm.	US-PGPUB	OR	ON	2006/03/30 13:53
L11	96	((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:H" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin:h")).clm.	US-PGPUB	OR	ON	2006/03/30 13:53

## EAST Search History

L12	48	((torr precursor plasma gate passivat\$6) and ((amorphous near2 (silicon adj nitride)) "a-sin.sub.x:h" "a-sin.sub.x h" "a-sin" "a-sin:h" "a-sin :h"))).clm.	US-PGPUB	OR	ON	2006/03/30 13:55
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